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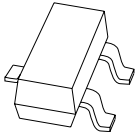
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Kind regards,

Team Nexperia



PBSS5140T

40 V, 1 A PNP low V_{CEsat} BISS transistor

Rev. 04 — 29 July 2008

Product data sheet

1. Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4140T.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation

1.3 Applications

- General-purpose switching and muting
- LCD backlighting
- Supply line switching circuits
- Battery-driven equipment (mobile phones, video cameras and handheld devices)

1.4 Quick reference data

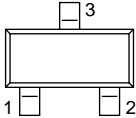
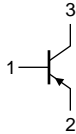
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-40	V
I_C	collector current		-	-	-1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	-2	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = -500$ mA; $I_B = -50$ mA	[1] -	300	< 500	m Ω

[1] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter		
3	collector		

006aab259

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5140T	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBSS5140T	*2H

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-40	V
V_{CEO}	collector-emitter voltage	open base	-	-40	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
I_C	collector current		-	-1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-2	A
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	-1	A

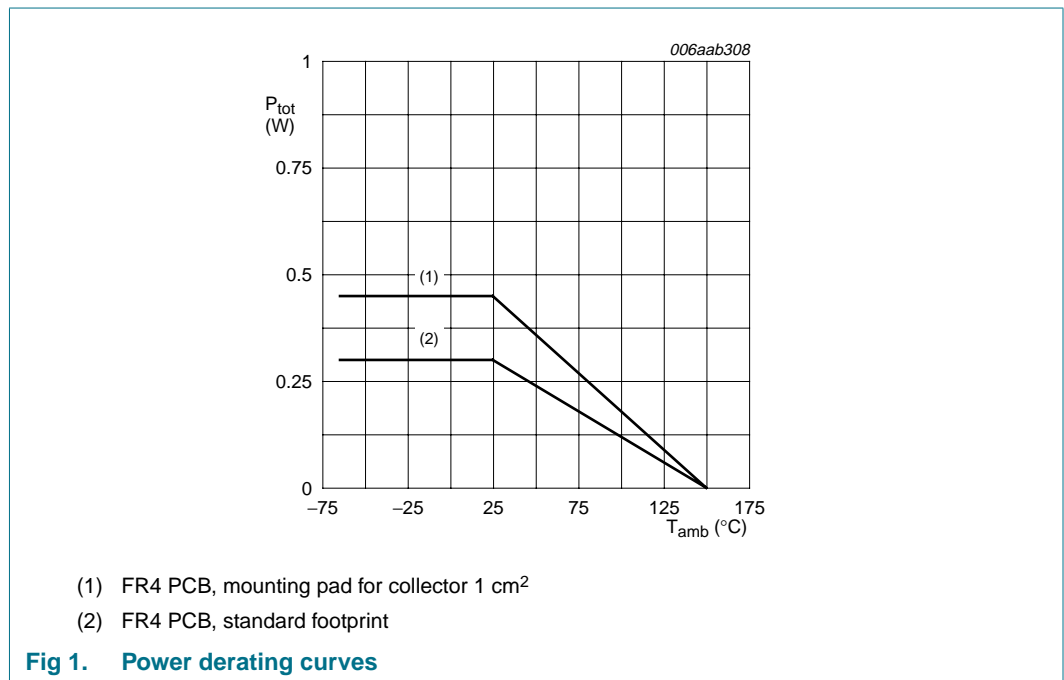
Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	[1] -	300	mW
			[2] -	450	mW
T_j	junction temperature		-	150	$^\circ\text{C}$
T_{amb}	ambient temperature		-65	+150	$^\circ\text{C}$
T_{stg}	storage temperature		-65	+150	$^\circ\text{C}$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



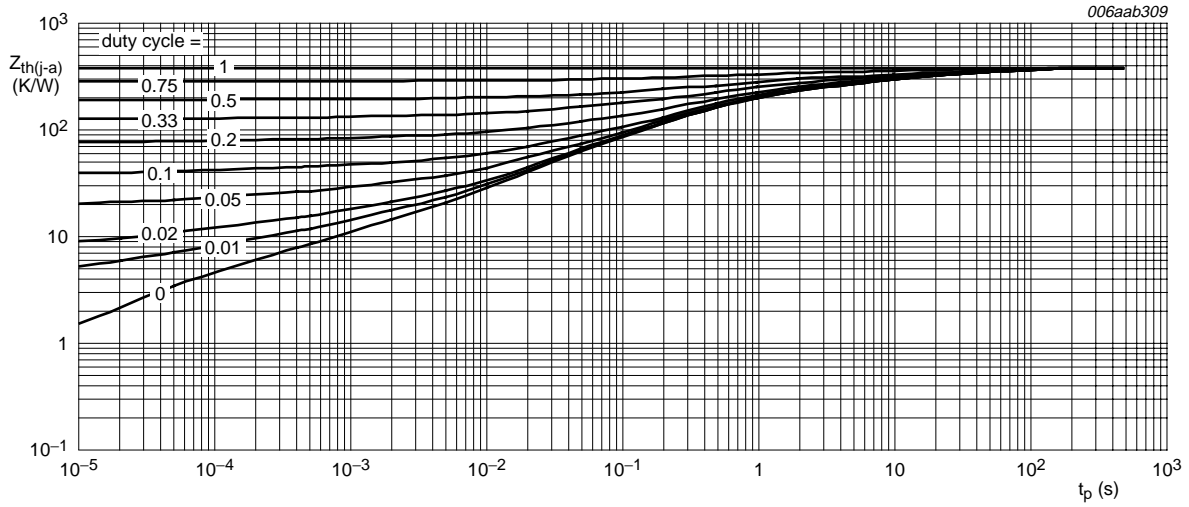
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	417	K/W
			[2] -	-	278	K/W

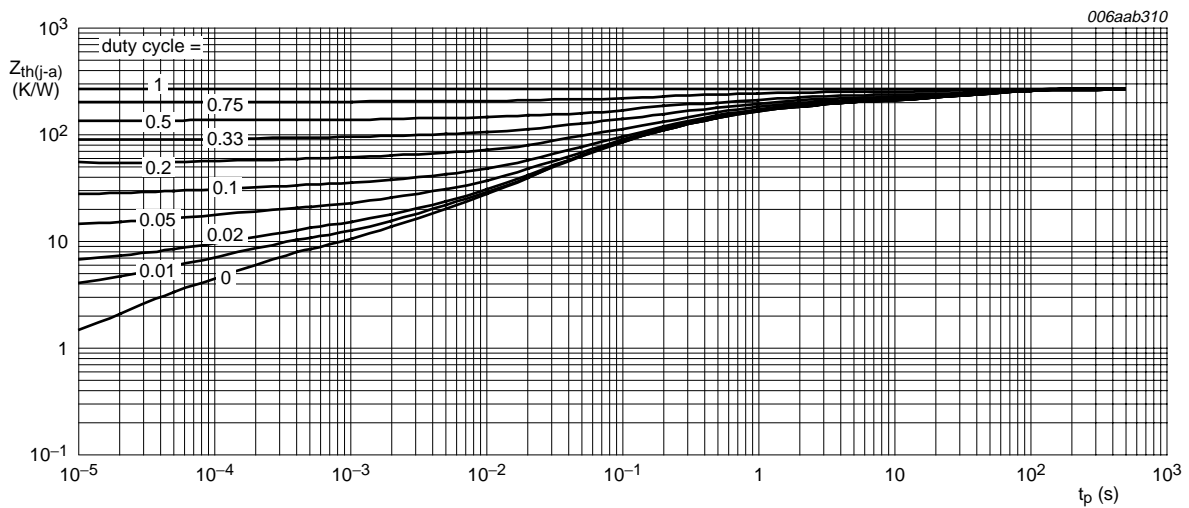
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 1 cm²

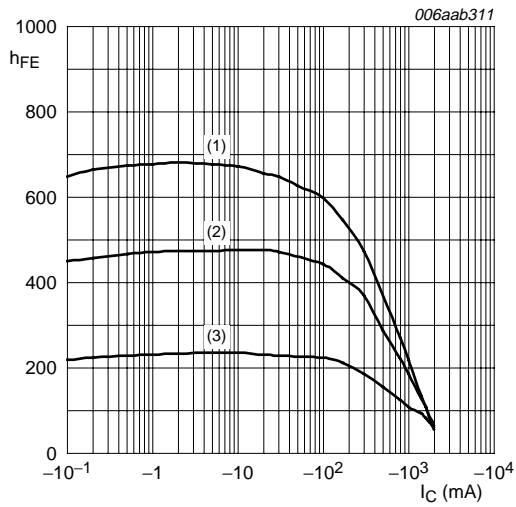
Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

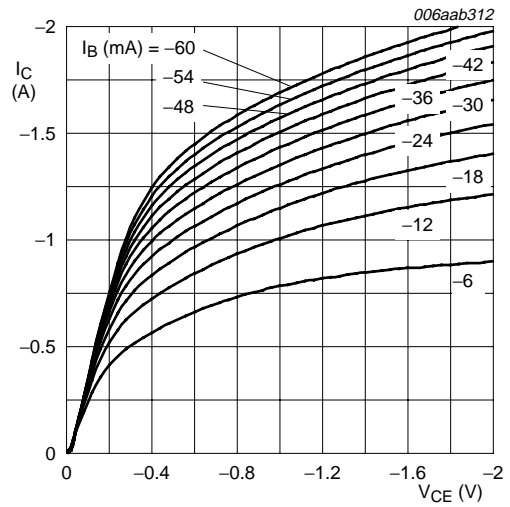
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -40\text{ V}; I_E = 0\text{ A}$	-	-	-100	nA
		$V_{CB} = -40\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	-50	μA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = -30\text{ V}; I_B = 0\text{ A}$	-	-	-100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	-	-	-100	nA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}; I_C = -1\text{ mA}$	300	-	-	
		$V_{CE} = -5\text{ V}; I_C = -100\text{ mA}$	300	-	800	
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$	[1] 250	-	-	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	[1] 160	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	-	-	-200	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	[1] -	-	-250	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$	[1] -	-	-500	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	[1] -	300	< 500	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA}$	[1] -	-	-1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	-	-	-1	V
t_d	delay time	$V_{CC} = -10\text{ V}; I_C = -0.5\text{ A}; I_{Bon} = -25\text{ mA}; I_{Boff} = 25\text{ mA}$	-	10	-	ns
t_r	rise time		-	31	-	ns
t_{on}	turn-on time		-	41	-	ns
t_s	storage time		-	195	-	ns
t_f	fall time		-	65	-	ns
t_{off}	turn-off time		-	260	-	ns
f_T	transition frequency	$V_{CE} = -10\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	150	-	-	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_E = 0\text{ A}; f = 1\text{ MHz}$	-	-	12	pF

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.



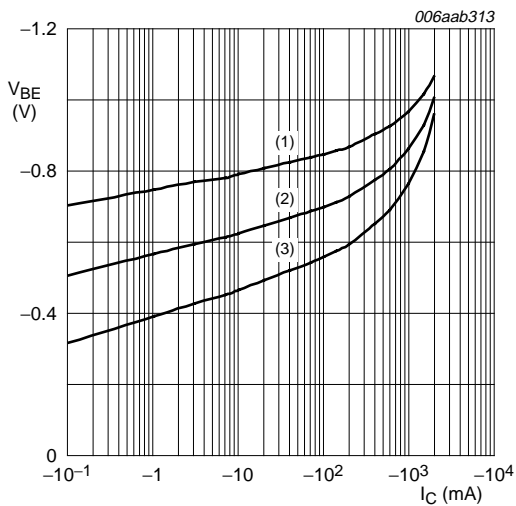
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = 100\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 4. DC current gain as a function of collector current; typical values



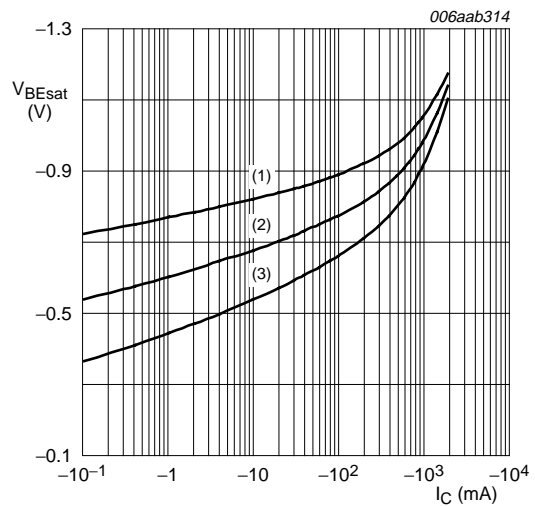
$T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig 5. Collector current as a function of collector-emitter voltage; typical values



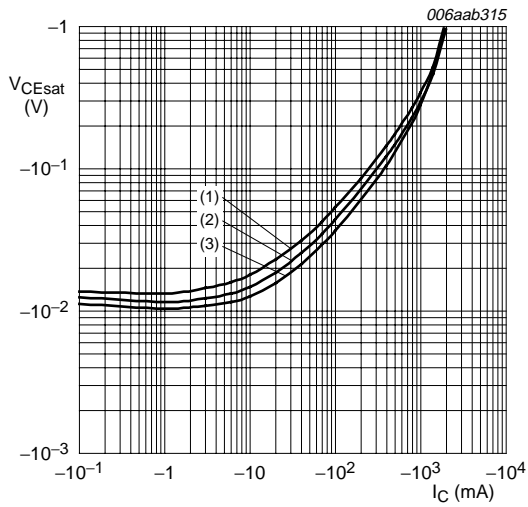
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 6. Base-emitter voltage as a function of collector current; typical values



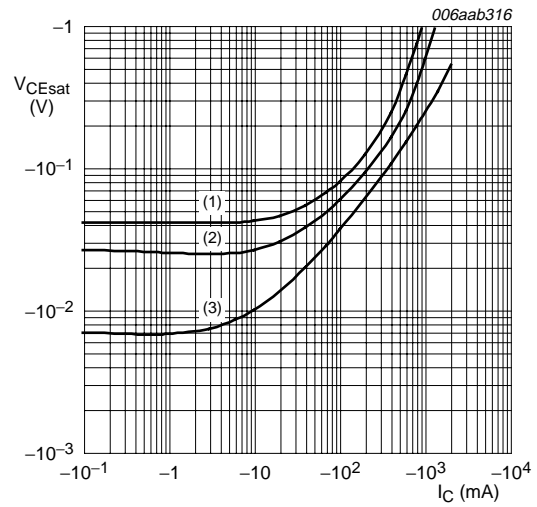
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 (3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 7. Base-emitter saturation voltage as a function of collector current; typical values



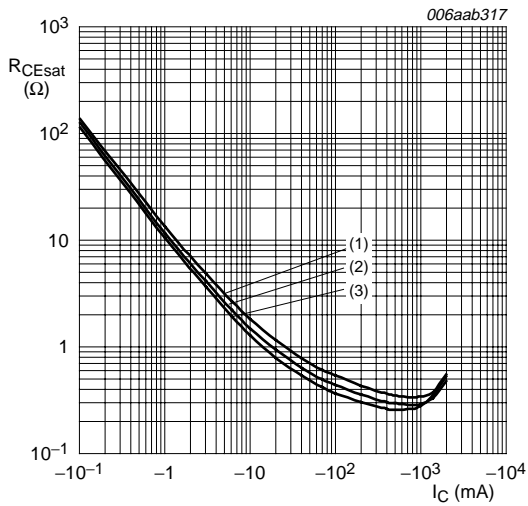
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



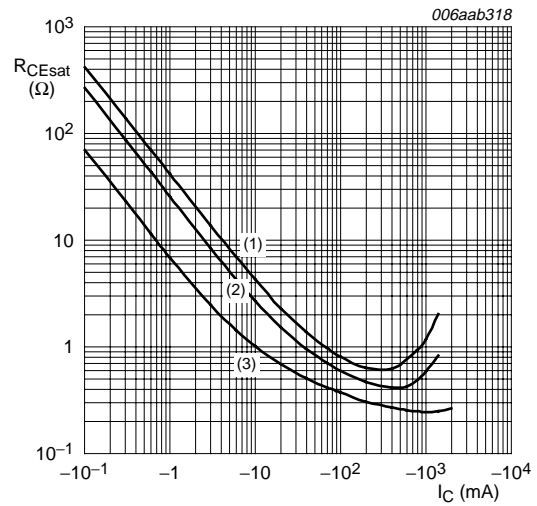
$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

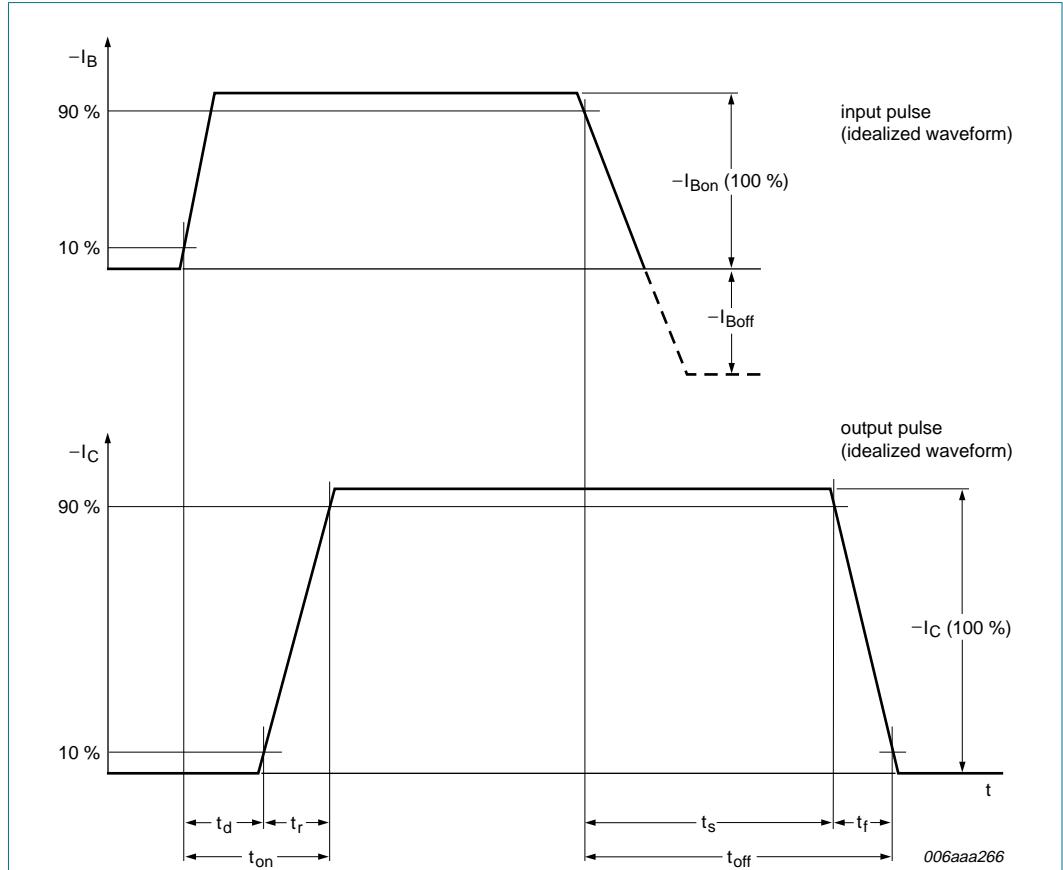
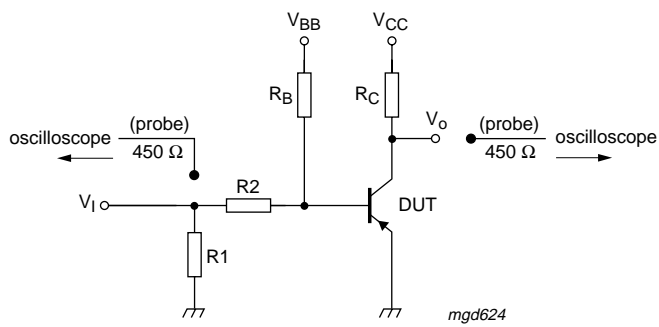


Fig 12. BISS transistor switching time definition



$V_{CC} = -10\text{ V}$; $I_C = -0.5\text{ A}$; $I_{B(on)} = -25\text{ mA}$; $I_{B(off)} = 25\text{ mA}$

Fig 13. Test circuit for switching times

9. Package outline

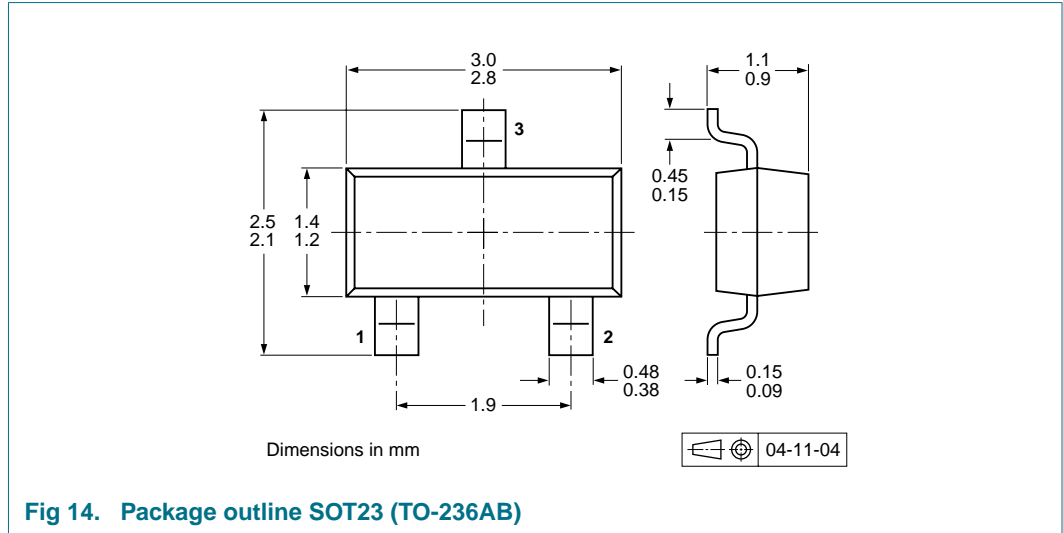


Fig 14. Package outline SOT23 (TO-236AB)

10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PBSS5140T	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see [Section 14](#).

11. Soldering

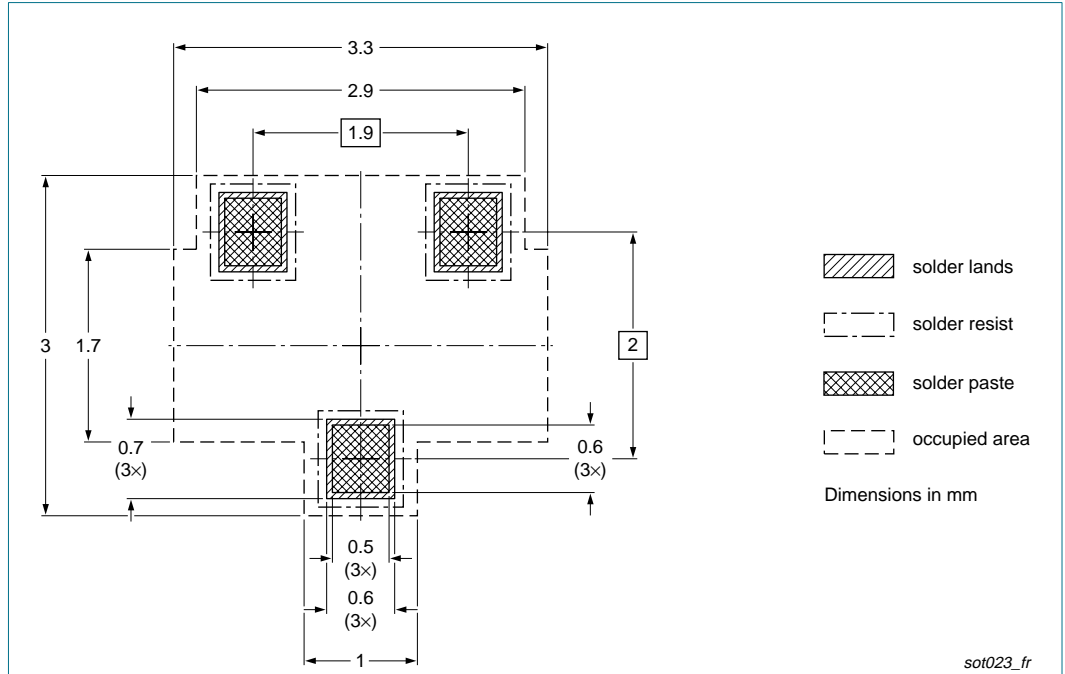


Fig 15. Reflow soldering footprint SOT23 (TO-236AB)

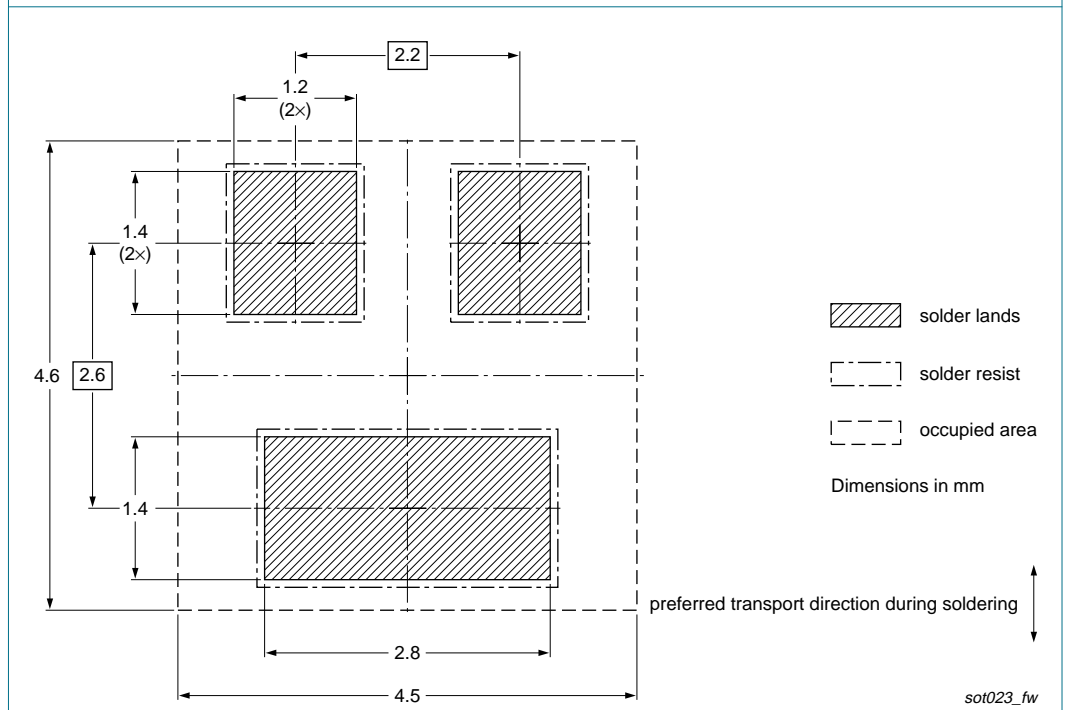


Fig 16. Wave soldering footprint SOT23 (TO-236AB)

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5140T_4	20080729	Product data sheet	-	PBSS5140T_3
Modifications:	<ul style="list-style-type: none"> • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 4 “Marking codes”: marking code corrected • Table 5 “Limiting values”: conditions added for I_{CM} and I_{BM} • Figure 1, 2 and 3: added • Table 7: R_{CEsat} redefined to collector-emitter saturation resistance • Figure 4, 6, 8 and 10: updated • Figure 5, 7, 9 and 11: added • Section 8 “Test information”: added • Figure 14: superseded by minimized package outline drawing • Section 11 “Soldering”: added • Section 13 “Legal information”: updated 			
PBSS5140T_3	20040107	Product specification	-	PBSS5140T_2
PBSS5140T_2	20010720	Product specification	-	PBSS5140T_1
PBSS5140T_1	20001116	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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